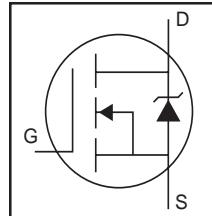


IRFB4615PbF

Applications

- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits

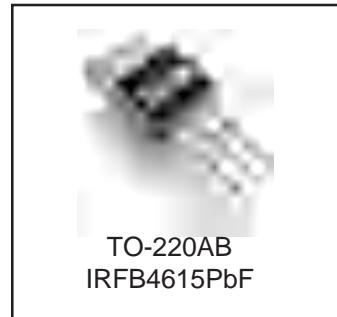


HEXFET® Power MOSFET

V_{DSS}	150V
R_{DS(on)} typ.	32mΩ
	max. 39mΩ
I_D	35A

Benefits

- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode dV/dt and dI/dt Capability
- Lead-Free



G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	35	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	25	
I _{DM}	Pulsed Drain Current ①	140	
P _D @ T _C = 25°C	Maximum Power Dissipation	144	W
	Linear Derating Factor	0.96	W/°C
V _{GS}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery ③	38	V/ns
T _J	Operating Junction and	-55 to + 175	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10lb·in (1.1N·m)	

Avalanche Characteristics

E _{AS} (Thermally limited)	Single Pulse Avalanche Energy ②	109	mJ
I _{AR}	Avalanche Current ①	See Fig. 14, 15, 22a, 22b,	A
E _{AR}	Repetitive Avalanche Energy ④		mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case ⑧	—	1.045	°C/W
R _{θCS}	Case-to-Sink, Flat, Greased Surface	0.50		
R _{θJA}	Junction-to-Ambient (PCB Mount) ⑦⑧	—	62	

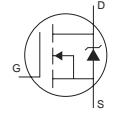
Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(\text{BR})\text{DSS}}$	Drain-to-Source Breakdown Voltage	150	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
$\Delta V_{(\text{BR})\text{DSS}}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.19	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 5\text{mA}$ ①
$R_{DS(\text{on})}$	Static Drain-to-Source On-Resistance	—	32	39	$\text{m}\Omega$	$V_{GS} = 10\text{V}, I_D = 21\text{A}$ ④
$V_{GS(\text{th})}$	Gate Threshold Voltage	3.0	—	5.0	V	$V_{DS} = V_{GS}, I_D = 100\mu\text{A}$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 150\text{V}, V_{GS} = 0\text{V}$
		—	—	250		$V_{DS} = 150\text{V}, V_{GS} = 0\text{V}, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20\text{V}$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20\text{V}$
$R_{G(\text{int})}$	Internal Gate Resistance	—	2.7	—	Ω	

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	35	—	—	S	$V_{DS} = 50\text{V}, I_D = 21\text{A}$
Q_g	Total Gate Charge	—	26	—	nC	$I_D = 21\text{A}$
Q_{gs}	Gate-to-Source Charge	—	8.6	—		$V_{DS} = 75\text{V}$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	9.0	—		$V_{GS} = 10\text{V}$ ④
Q_{sync}	Total Gate Charge Sync. ($Q_g - Q_{gd}$)	—	17	—		$I_D = 21\text{A}, V_{DS} = 0\text{V}, V_{GS} = 10\text{V}$
$t_{d(on)}$	Turn-On Delay Time	—	15	—	ns	$V_{DD} = 98\text{V}$
t_r	Rise Time	—	35	—		$I_D = 21\text{A}$
$t_{d(off)}$	Turn-Off Delay Time	—	25	—		$R_G = 7.3\Omega$
t_f	Fall Time	—	20	—		$V_{GS} = 10\text{V}$ ④
C_{iss}	Input Capacitance	—	1750	—	pF	$V_{GS} = 0\text{V}$
C_{oss}	Output Capacitance	—	155	—		$V_{DS} = 50\text{V}$
C_{rss}	Reverse Transfer Capacitance	—	40	—		$f = 1.0\text{MHz}$ (See Fig.5)
$C_{oss \text{ eff. (ER)}}$	Effective Output Capacitance (Energy Related) ⑥	—	179	—		$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}$ to 120V ⑥(See Fig.11)
$C_{oss \text{ eff. (TR)}}$	Effective Output Capacitance (Time Related) ⑤	—	382	—		$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}$ to 120V ⑤

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_s	Continuous Source Current (Body Diode)	—	—	35	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{sM}	Pulsed Source Current (Body Diode) ①	—	—	140		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_s = 21\text{A}, V_{GS} = 0\text{V}$ ④
t_{rr}	Reverse Recovery Time	—	70	—	ns	$T_J = 25^\circ\text{C}$ $V_R = 100\text{V}$,
		—	83	—		$T_J = 125^\circ\text{C}$ $I_F = 21\text{A}$
Q_{rr}	Reverse Recovery Charge	—	177	—	nC	$T_J = 25^\circ\text{C}$ $di/dt = 100\text{A}/\mu\text{s}$ ④
		—	247	—		$T_J = 125^\circ\text{C}$
I_{RRM}	Reverse Recovery Current	—	4.9	—	A	$T_J = 25^\circ\text{C}$
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Limited by $T_{J\text{max}}$, starting $T_J = 25^\circ\text{C}$, $L = 0.51\text{mH}$

$R_G = 25\Omega, I_{AS} = 21\text{A}, V_{GS} = 10\text{V}$. Part not recommended for use above this value .

③ $I_{SD} \leq 21\text{A}$, $di/dt \leq 549\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(\text{BR})\text{DSS}}$, $T_J \leq 175^\circ\text{C}$.

④ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.

⑤ $C_{oss \text{ eff. (TR)}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⑥ $C_{oss \text{ eff. (ER)}}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994

⑧ R_θ is measured at T_J approximately 90°C

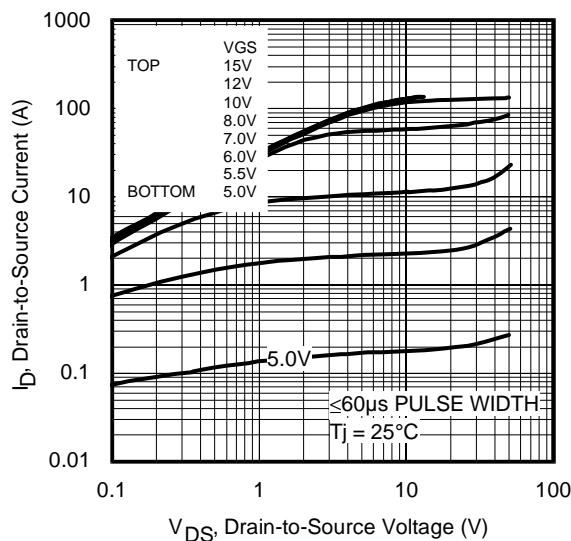


Fig 1. Typical Output Characteristics

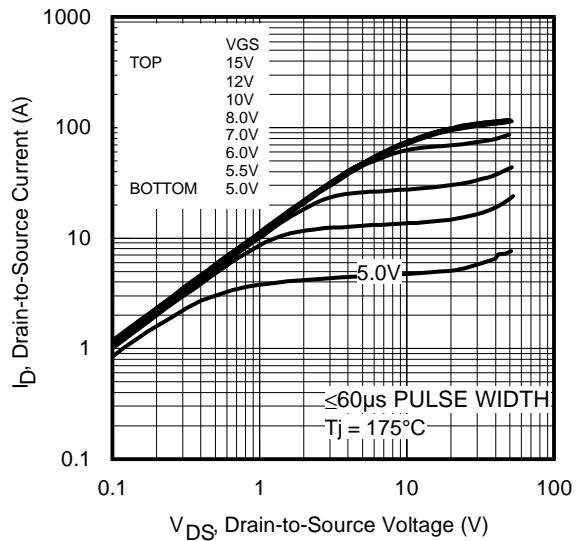


Fig 2. Typical Output Characteristics

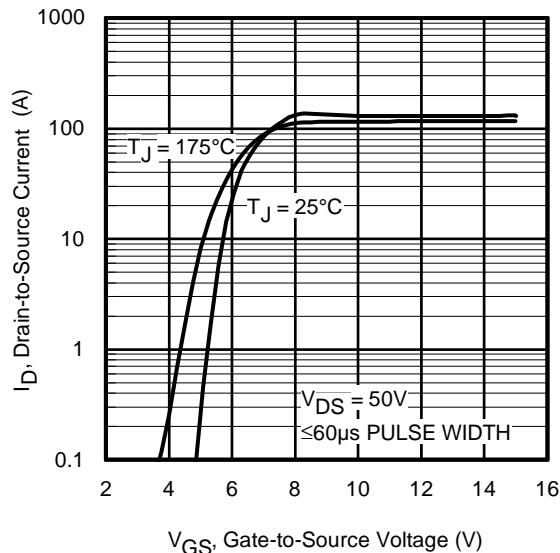


Fig 3. Typical Transfer Characteristics

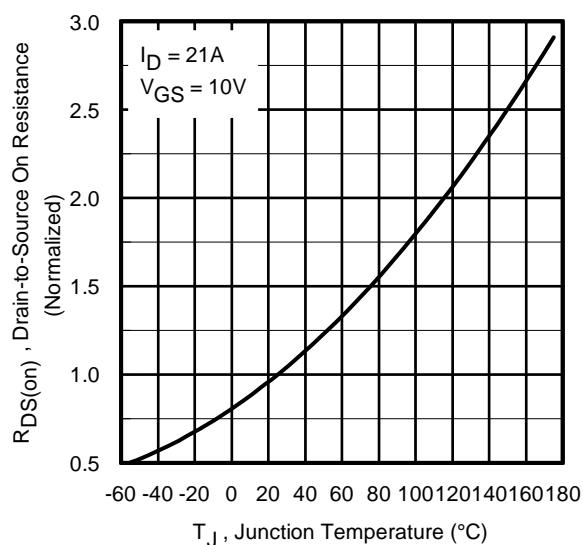


Fig 4. Normalized On-Resistance vs. Temperature

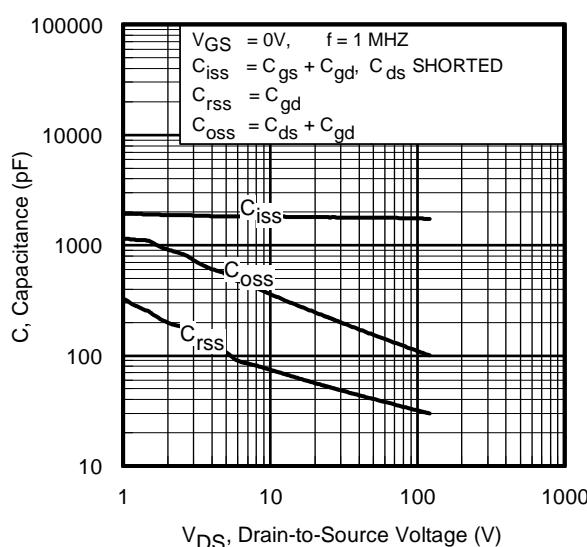


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

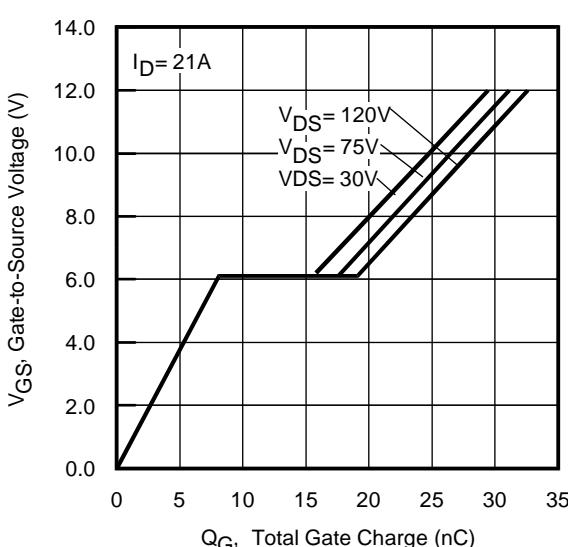


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

IRFB4615PbF

International
Rectifier

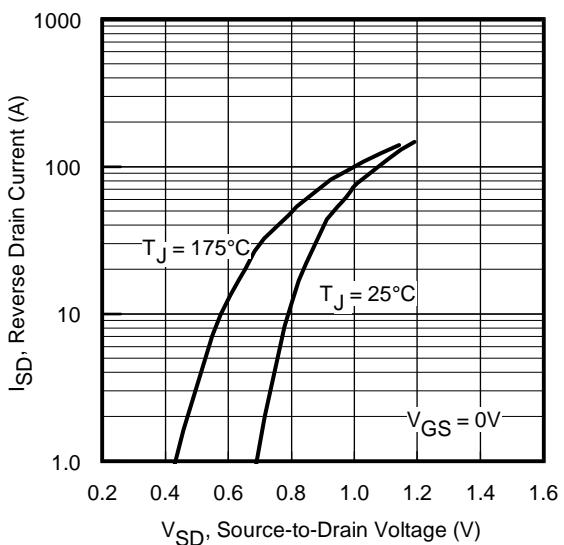


Fig 7. Typical Source-Drain Diode Forward Voltage

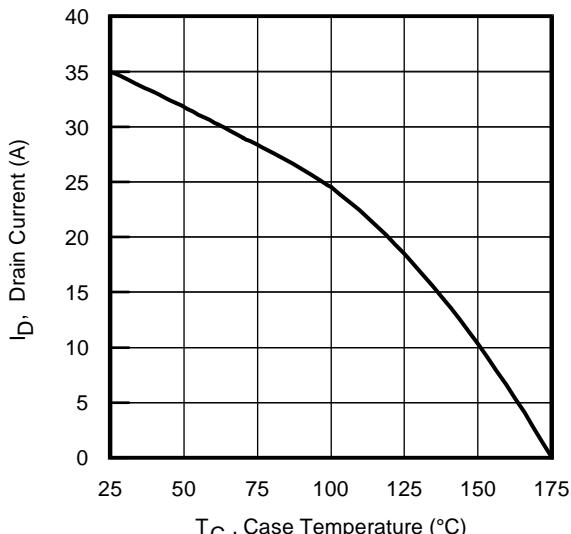


Fig 9. Maximum Drain Current vs. Case Temperature

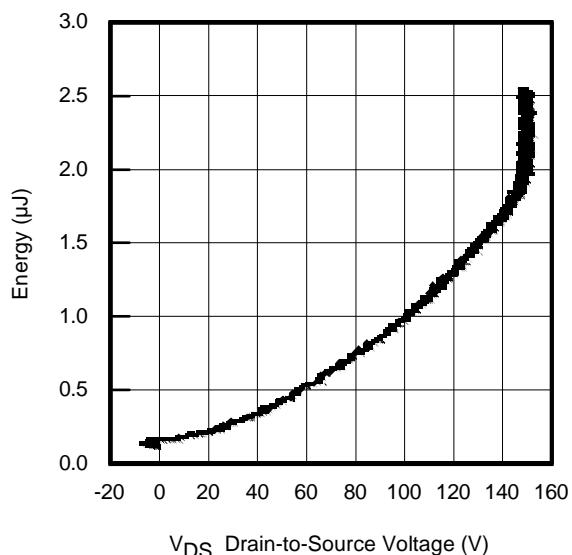


Fig 11. Typical C_{oss} Stored Energy

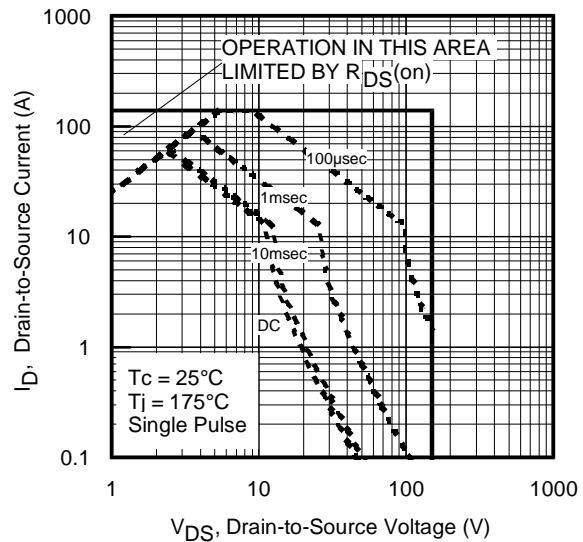


Fig 8. Maximum Safe Operating Area

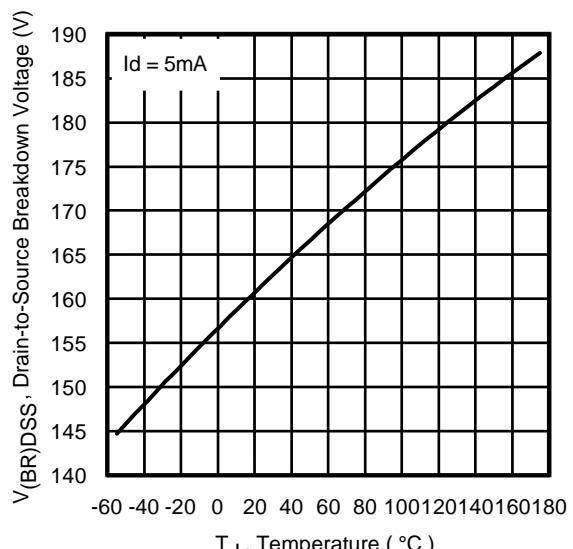


Fig 10. Drain-to-Source Breakdown Voltage

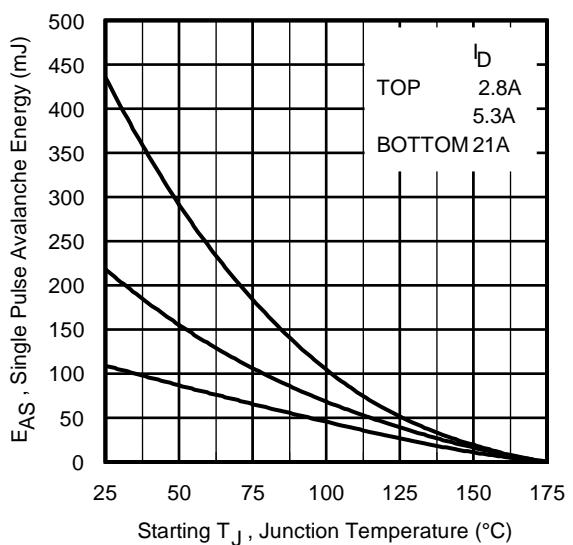


Fig 12. Maximum Avalanche Energy vs. Drain Current

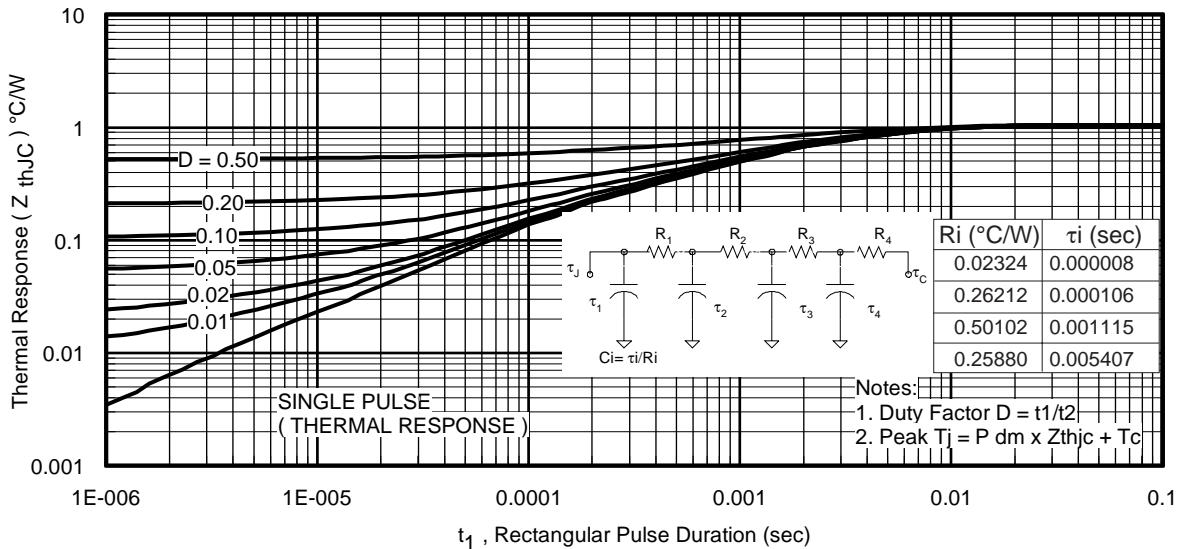


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

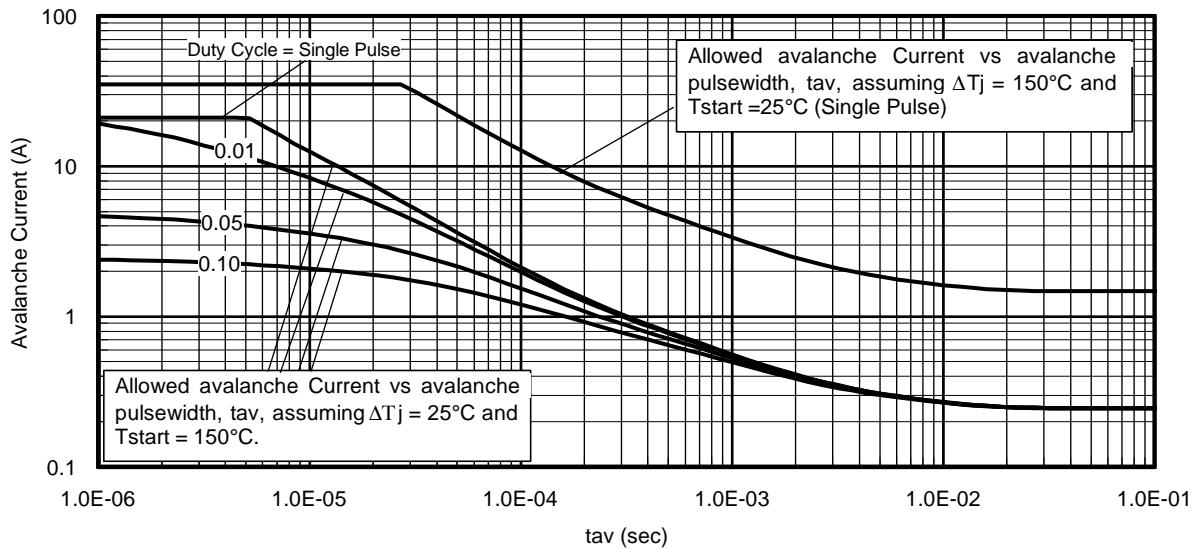
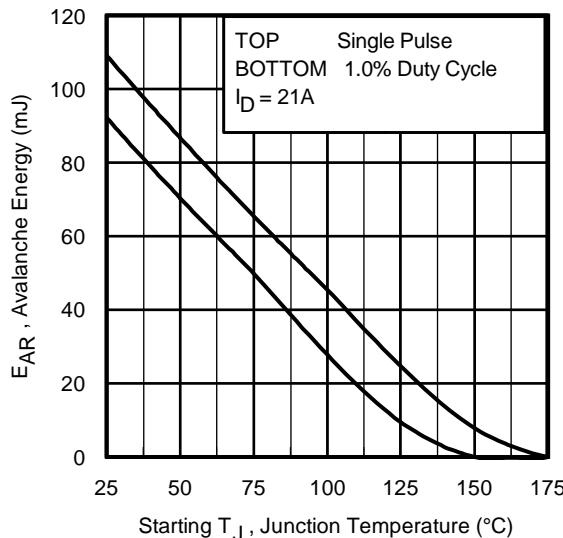


Fig 14. Typical Avalanche Current vs.Pulsewidth

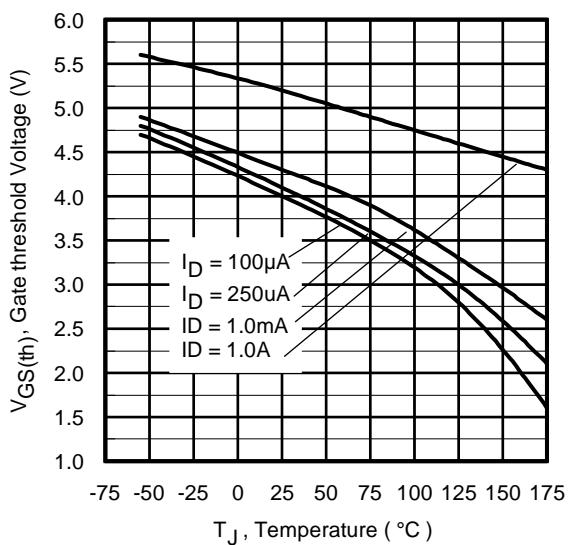
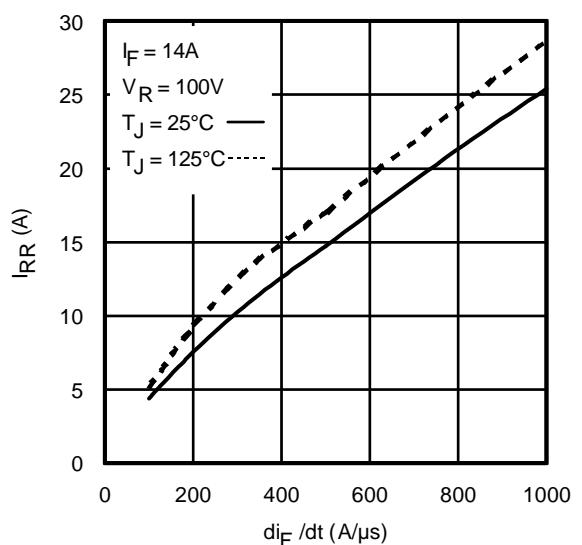
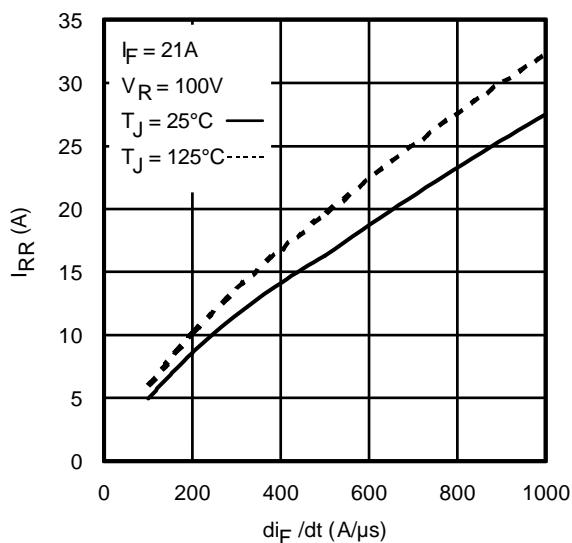
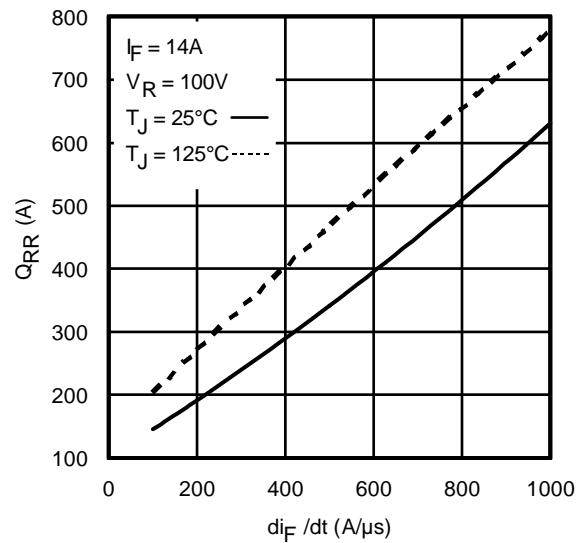
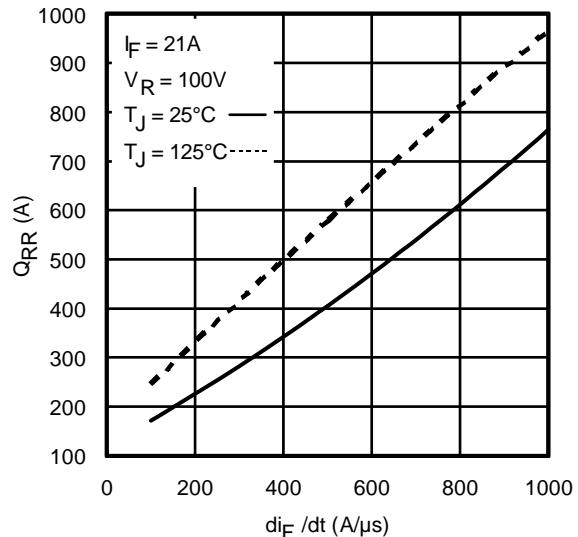


Notes on Repetitive Avalanche Curves , Figures 14, 15:
(For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption: Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 16a, 16b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 15).
- t_{av} = Average time in avalanche.
- D = Duty cycle in avalanche = $t_{av} \cdot f$
- $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13

$$\begin{aligned} P_{D(ave)} &= 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC} \\ I_{av} &= 2\Delta T / [1.3 \cdot BV \cdot Z_{th}] \\ E_{AS(AR)} &= P_{D(ave)} \cdot t_{av} \end{aligned}$$

Fig 15. Maximum Avalanche Energy vs. Temperature

**Fig. 16.** Threshold Voltage vs. Temperature**Fig. 17 -** Typical Recovery Current vs. di_f/dt **Fig. 18 -** Typical Recovery Current vs. di_f/dt **Fig. 19 -** Typical Stored Charge vs. di_f/dt **Fig. 20 -** Typical Stored Charge vs. di_f/dt

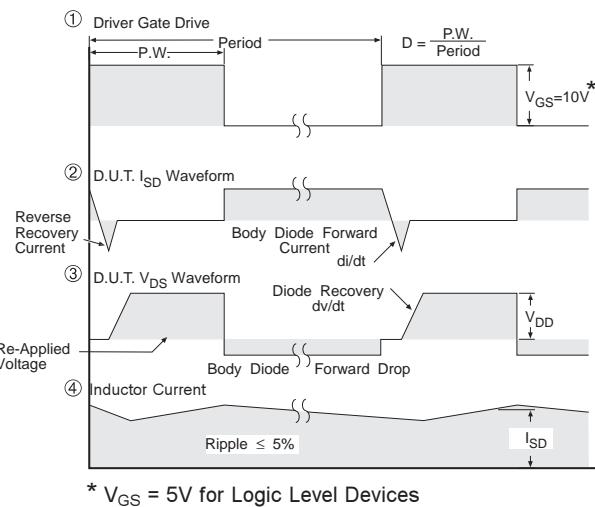
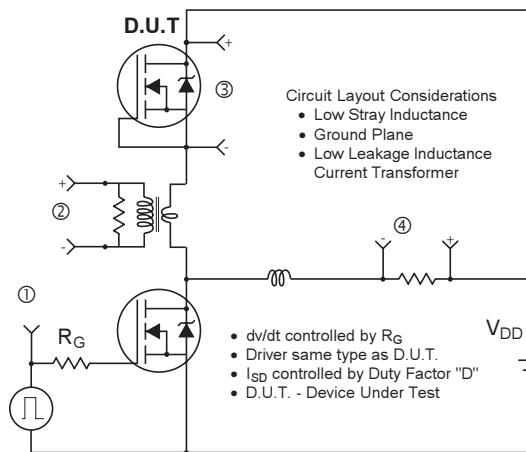


Fig 21. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

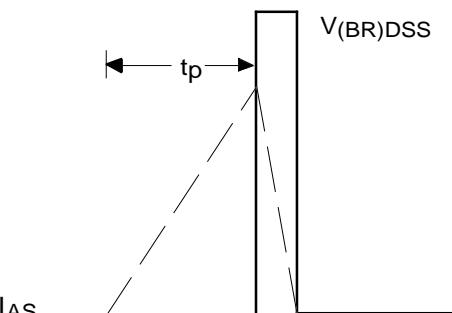
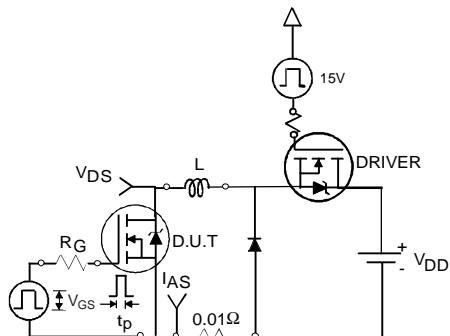


Fig 22a. Unclamped Inductive Test Circuit

Fig 22b. Unclamped Inductive Waveforms

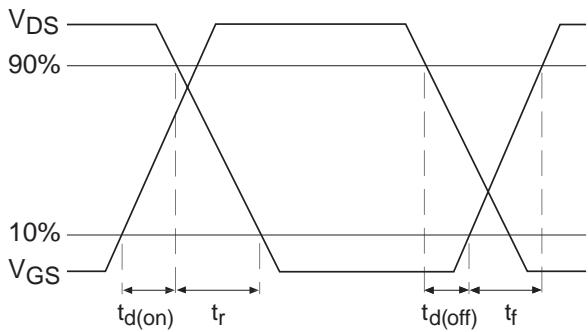
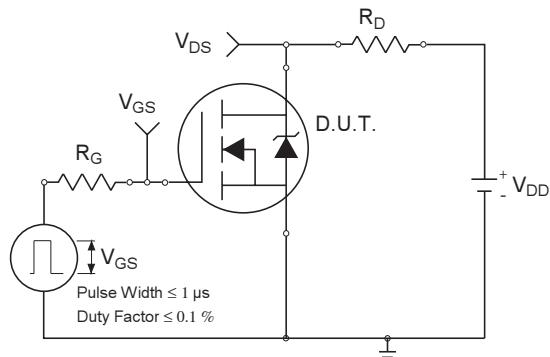


Fig 23a. Switching Time Test Circuit

Fig 23b. Switching Time Waveforms

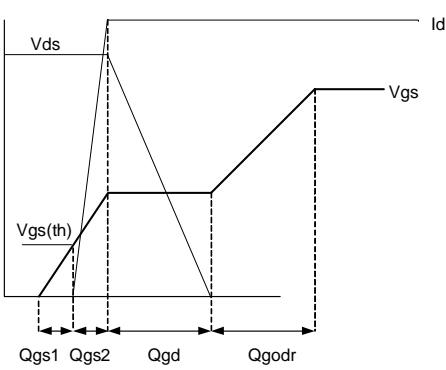
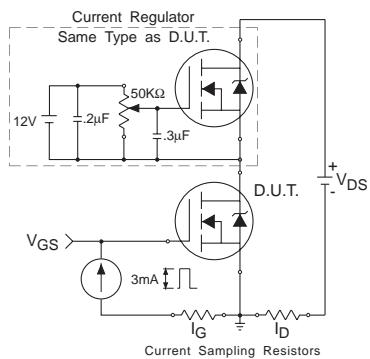
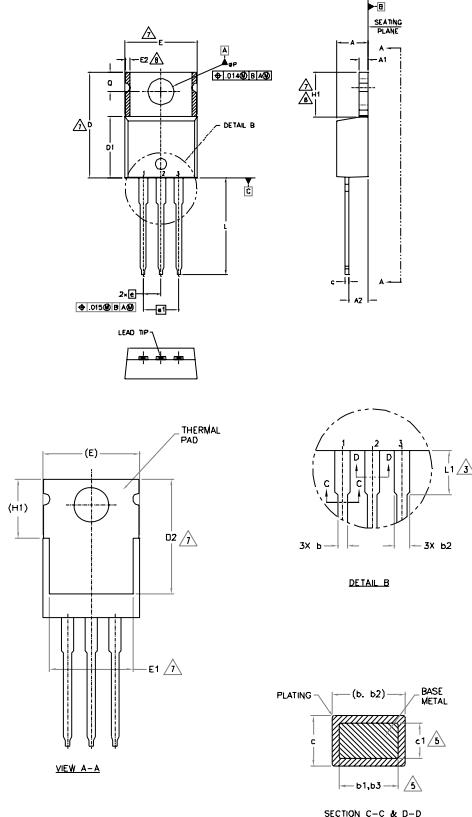


Fig 24a. Gate Charge Test Circuit

Fig 24b. Gate Charge Waveform

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1 - DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M-1994.
- 2 - DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
- 3 - LEAD DIMENSION AND FINISH UNCONTROLLED IN LT.
- 4 - DIMENSION E1 IS THE TOTAL LENGTH OF THE LEAD. NO. OF LEADS, MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
- 5 - DIMENSION b1, b2 & c1 APPLY TO BASE METAL ONLY.
- 6 - CONTROLLING DIMENSION : INCHES
- 7 - THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E1, D2 & E1
- 8 - DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRRREGULARITIES ARE ALLOWED.
- 9 - OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.97	.015	.038	5
b2	1.14	1.78	.045	.070	5
b3	1.14	1.73	.045	.068	
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	11.68	12.88	.460	.507	7
E	9.65	10.67	.380	.420	4,7
E1	6.86	8.89	.270	.350	7
E2	-	0.76	-	.030	8
e	2.54 BSC		.100 BSC		
e1	5.08 BSC		.200 BSC		7,8
H1	5.84	6.86	.230	.270	
L	12.70	14.73	.500	.580	
L1	3.56	4.06	.140	.160	3
oP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	

LEAD ASSIGNMENTS

- 1 - GATE
- 2 - DRAIN
- 3 - SOURCE

INPUT CAPACIT

- 1 - GATE
- 2 - COLLECTOR
- 3 - Emitter

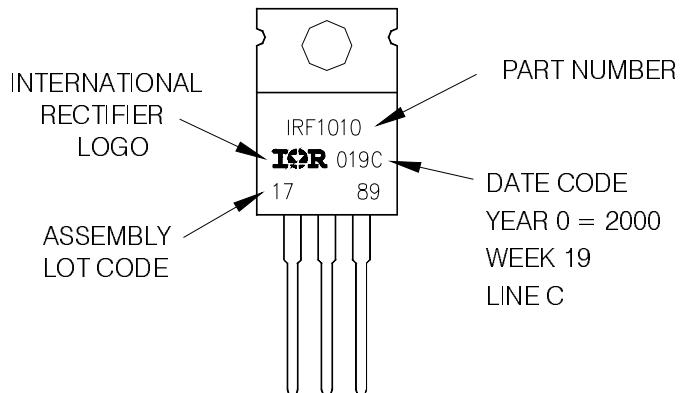
DIODES

- 1 - ANODE
- 2 - CATHODE
- 3 - ANODE

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
 LOT CODE 1789
 ASSEMBLED ON WW 19, 2000
 IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead - Free"



TO-220AB packages are not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Data and specifications subject to change without notice.
 This product has been designed and qualified for the Industrial market.
 Qualification Standards can be found on IR's Web site.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105

TAC Fax: (310) 252-7903

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